



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

MMSTA92 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.3 A

Collector-base voltage

$V_{(BR)CBO}$: -310 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-310			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-305			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -200V, I_E = 0$			-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -1 mA$	60			
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -10 mA$	100		200	
	$h_{FE(3)}$	$V_{CE} = -10 V, I_C = -80 mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 mA, I_B = -2 mA$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 mA, I_B = -2 mA$			-0.9	V
Transition frequency	f_T	$V_{CE} = -20 V, I_C = -10 mA$ $f = 30MHz$	50			MHz

DEVICE MARKING

MMSTA92=K3R